

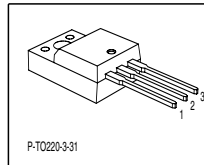
## Cool MOS™ Power Transistor

### Feature

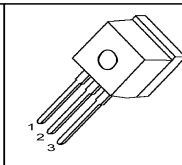
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme  $dv/dt$  rated
- High peak current capability
- Improved transconductance
- P-TO-220-3-31: Fully isolated package (2500 VAC; 1 minute)

$V_{DS} @ T_{jmax}$	730	V
$R_{DS(on)}$	0.6	$\Omega$
$I_D$	7.3	A

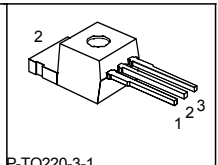
P-TO220-3-31



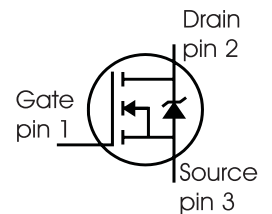
P-TO262-3-1



P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP07N65C3	P-TO220-3-1	Q67040-S4624	07N65C3
SPI07N65C3	P-TO262-3-1	Q67040-S4623	07N65C3
SPA07N65C3	P-TO220-3-31	Q67040-S4622	07N65C3



### Maximum Ratings

Parameter	Symbol	Value		Unit
		SPP_I	SPA	
Continuous drain current $T_C = 25\text{ }^\circ\text{C}$ $T_C = 100\text{ }^\circ\text{C}$	$I_D$	7.3 4.6	7.3 <sup>1)</sup> 4.6 <sup>1)</sup>	A
Pulsed drain current, $t_p$ limited by $T_{jmax}$	$I_{D\text{ puls}}$	21.9	21.9	A
Avalanche energy, single pulse $I_D=1.5\text{A}$ , $V_{DD}=50\text{V}$	$E_{AS}$	230	230	mJ
Avalanche energy, repetitive $t_{AR}$ limited by $T_{jmax}$ <sup>2)</sup> $I_D=2.5\text{A}$ , $V_{DD}=50\text{V}$	$E_{AR}$	0.5	0.5	
Avalanche current, repetitive $t_{AR}$ limited by $T_{jmax}$	$I_{AR}$	2.5	2.5	A
Gate source voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Gate source voltage AC ( $f > 1\text{Hz}$ )	$V_{GS}$	$\pm 30$	$\pm 30$	
Power dissipation, $T_C = 25\text{ }^\circ\text{C}$	$P_{tot}$	83	32	W
Operating and storage temperature	$T_j, T_{stg}$	-55...+150		$^\circ\text{C}$

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 480\text{ V}$ , $I_D = 7.3\text{ A}$ , $T_j = 125\text{ °C}$	$dv/dt$	50	V/ns

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.5	K/W
Thermal resistance, junction - case, FullPAK	$R_{thJC\text{ FP}}$	-	-	3.9	
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62	
Thermal resistance, junction - ambient, FullPAK	$R_{thJA\text{ FP}}$	-	-	80	
SMD version, device on PCB: @ min. footprint @ 6 cm <sup>2</sup> cooling area <sup>3)</sup>	$R_{thJA}$	-	-	62	
		-	35	-	
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	$T_{sold}$	-	-	260	°C

**Electrical Characteristics, at  $T_j=25\text{ °C}$  unless otherwise specified**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$ , $I_D=0.25\text{ mA}$	650	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{ V}$ , $I_D=2.5\text{ A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=350\text{ }\mu\text{A}$ , $V_{GS}=V_{DS}$	2.1	3	3.9	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$ $T_j=150\text{ °C}$	-	0.5	1	$\mu\text{A}$
			-	-	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$ , $I_D=4.6\text{ A}$ $T_j=25\text{ °C}$ $T_j=150\text{ °C}$	-	0.54	0.6	$\Omega$
			-	1.46	-	
Gate input resistance	$R_G$	$f=1\text{ MHz}$ , open drain	-	0.8	-	

**Electrical Characteristics**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 4.6A$	-	6	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0V$ , $V_{DS} = 25V$ , $f = 1MHz$	-	790	-	pF
Output capacitance	$C_{oss}$		-	260	-	
Reverse transfer capacitance	$C_{rss}$		-	16	-	
Effective output capacitance, <sup>4)</sup> energy related	$C_{o(er)}$	$V_{GS} = 0V$ , $V_{DS} = 0V$ to 480V	-	30	-	
Effective output capacitance, <sup>5)</sup> time related	$C_{o(tr)}$		-	55	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 380V$ , $V_{GS} = 0/13V$ , $I_D = 7.3A$ , $R_G = 12\Omega$ , $T_j = 125^{\circ}C$	-	6	-	ns
Rise time	$t_r$		-	3.5	-	
Turn-off delay time	$t_{d(off)}$		-	60	100	
Fall time	$t_f$		-	7	15	

### Gate Charge Characteristics

Gate to source charge	$Q_{gs}$	$V_{DD} = 480\text{V}$ , $I_D = 7.3\text{A}$	-	3	-	nC
Gate to drain charge	$Q_{gd}$		-	9.2	-	
Gate charge total	$Q_g$	$V_{DD} = 480\text{V}$ , $I_D = 7.3\text{A}$ , $V_{GS} = 0 \text{ to } 10\text{V}$	-	21	27	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 480\text{V}$ , $I_D = 7.3\text{A}$	-	5.5	-	V

<sup>1</sup>Limited only by maximum temperature

<sup>2</sup>Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV} = E_{AR} \cdot f$ .

<sup>3</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.

<sup>4</sup> $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

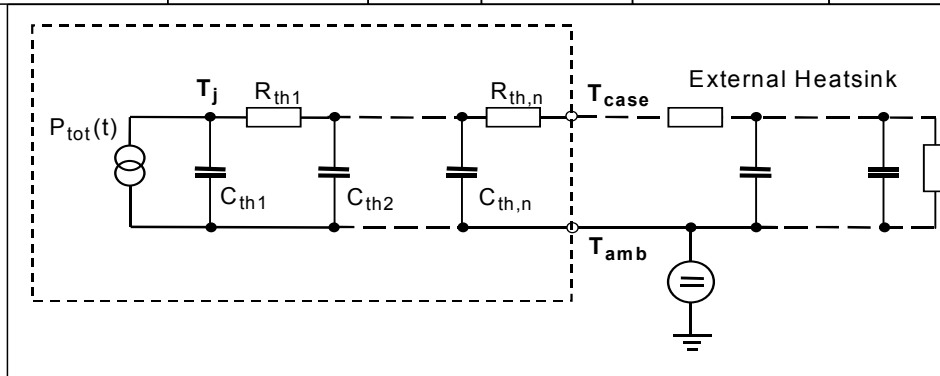
<sup>5</sup> $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

## Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	$I_S$	$T_C=25^{\circ}\text{C}$	-	-	7.3	A
Inverse diode direct current, pulsed	$I_{SM}$		-	-	21.9	
Inverse diode forward voltage	$V_{SD}$	$V_{GS}=0\text{V}$ , $I_F=I_S$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=480\text{V}$ , $I_F=I_S$ , $di_F/dt=100\text{A}/\mu\text{s}$	-	400	600	ns
Reverse recovery charge	$Q_{rr}$		-	4	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	28	-	A
Peak rate of fall of reverse recovery current	$di_{rr}/dt$	$T_j=25^{\circ}\text{C}$	-	800	-	$\text{A}/\mu\text{s}$

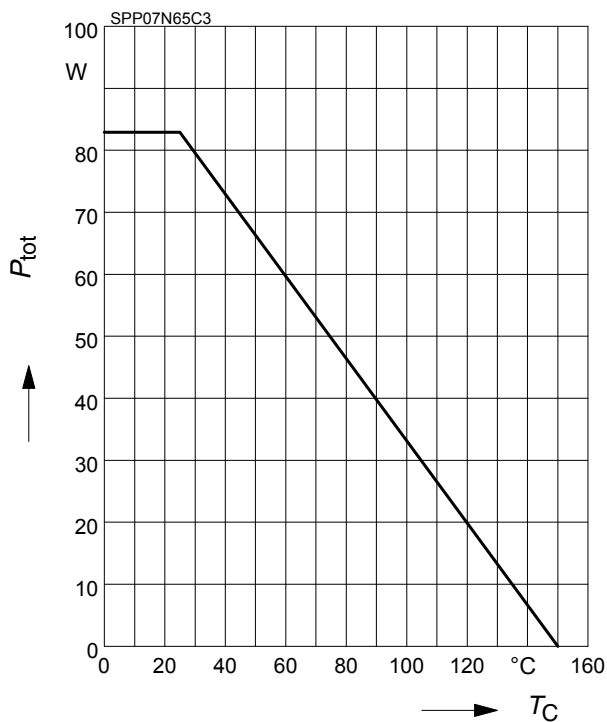
## Typical Transient Thermal Characteristics

Symbol	Value		Unit	Symbol	Value		Unit
	SPP_I	SPA			SPP_I	SPA	
$R_{th1}$	0.024	0.024	K/W	$C_{th1}$	0.00012	0.00012	Ws/K
$R_{th2}$	0.046	0.046		$C_{th2}$	0.0004578	0.0004578	
$R_{th3}$	0.085	0.085		$C_{th3}$	0.000645	0.000645	
$R_{th4}$	0.308	0.195		$C_{th4}$	0.001867	0.001867	
$R_{th5}$	0.317	0.45		$C_{th5}$	0.004795	0.007558	
$R_{th6}$	0.112	2.511		$C_{th6}$	0.045	0.412	



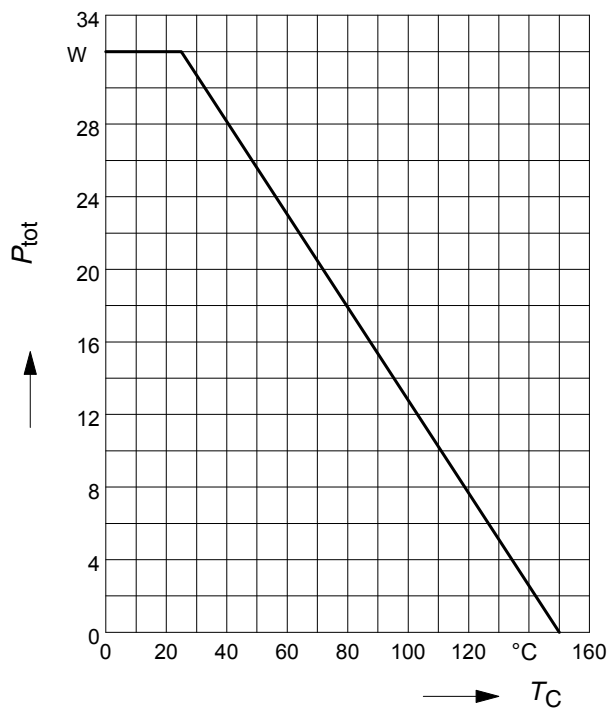
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



### 2 Power dissipation FullPAK

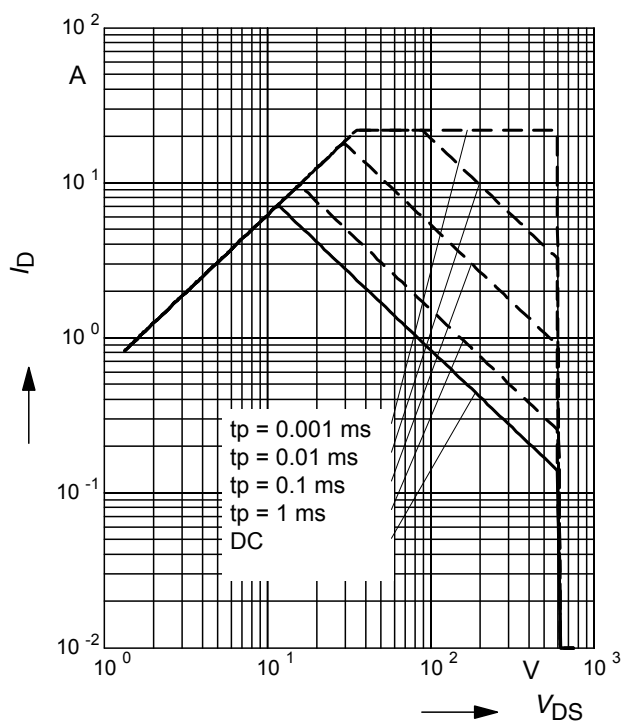
$$P_{\text{tot}} = f(T_C)$$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

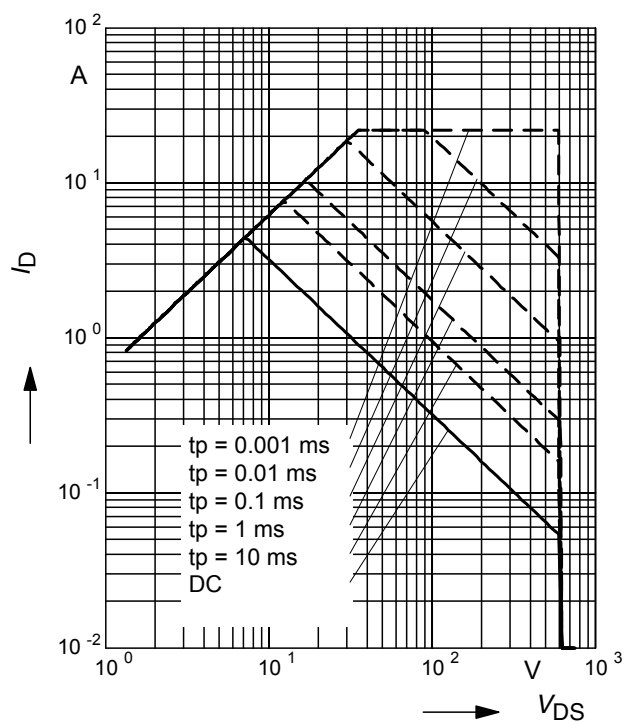
parameter :  $D = 0$  ,  $T_C = 25^\circ\text{C}$



### 4 Safe operating area FullPAK

$$I_D = f(V_{DS})$$

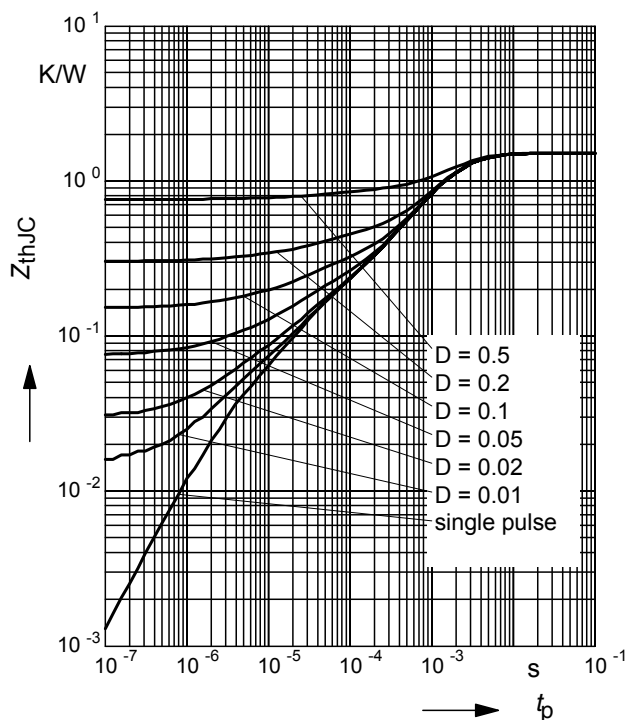
parameter:  $D = 0$  ,  $T_C = 25^\circ\text{C}$



## 5 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

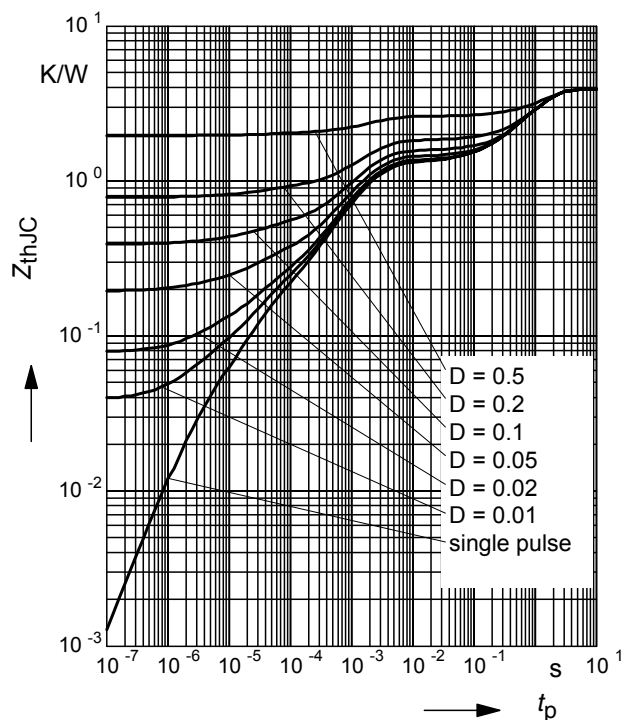
parameter:  $D = t_p/T$



## 6 Transient thermal impedance FullPAK

$$Z_{thJC} = f(t_p)$$

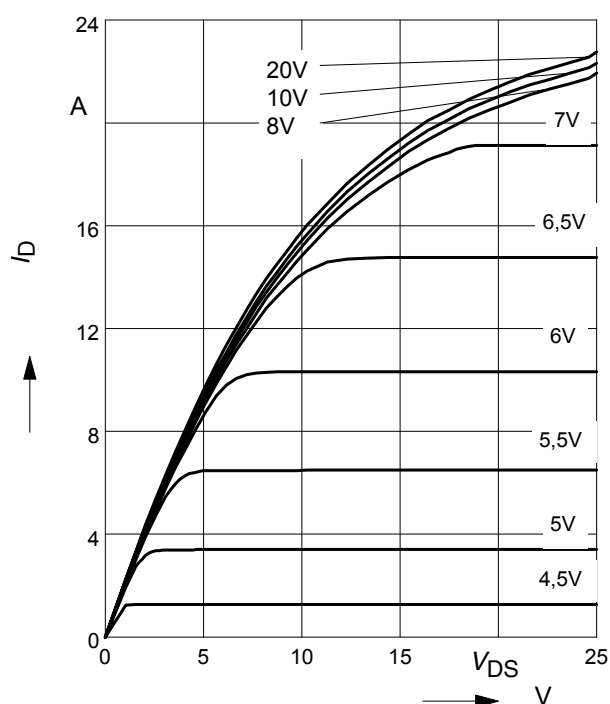
parameter:  $D = t_p/t$



## 7 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

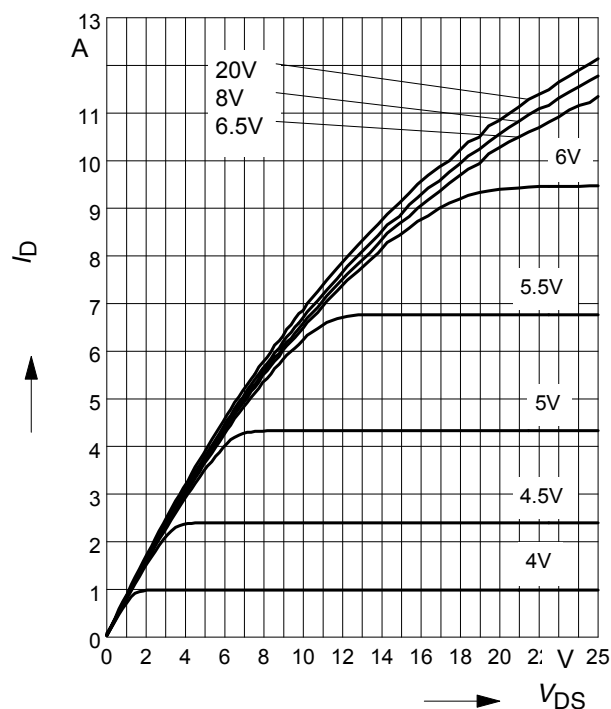
parameter:  $t_p = 10 \mu\text{s}, V_{GS}$



## 8 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$$

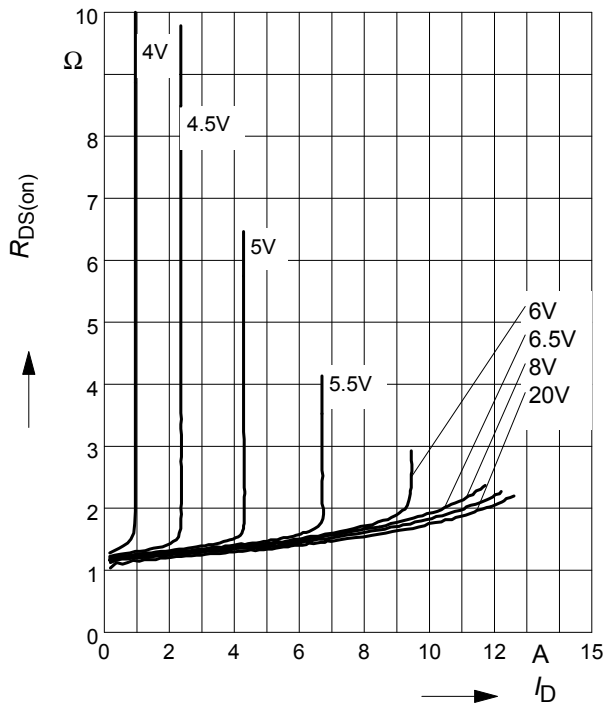
parameter:  $t_p = 10 \mu\text{s}, V_{GS}$



### 9 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

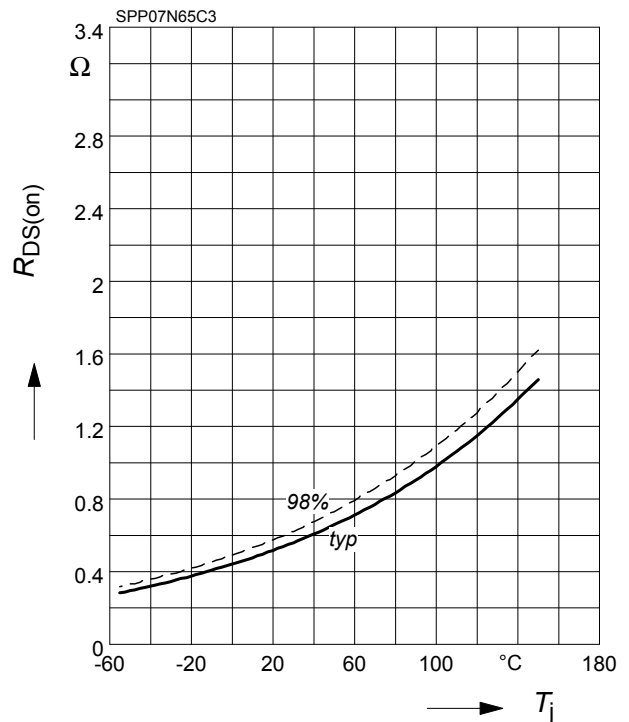
parameter:  $T_j = 150^\circ\text{C}$ ,  $V_{GS}$



### 10 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

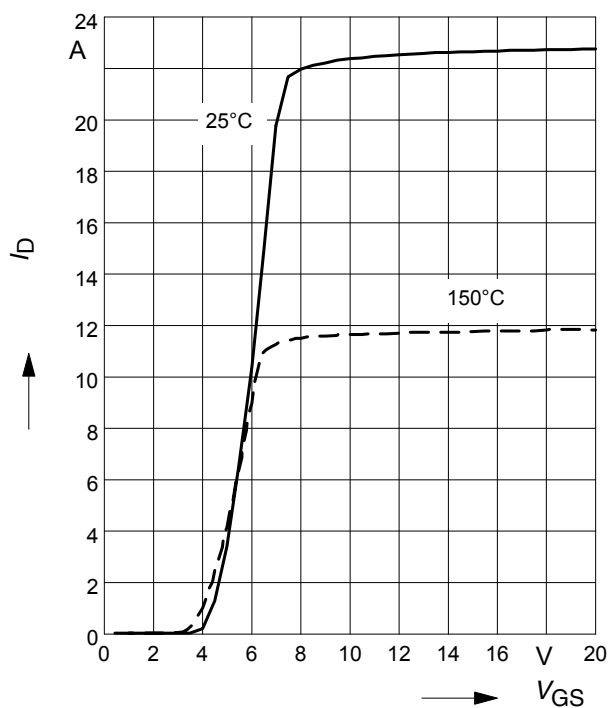
parameter:  $I_D = 4.6\text{ A}$ ,  $V_{GS} = 10\text{ V}$



### 11 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

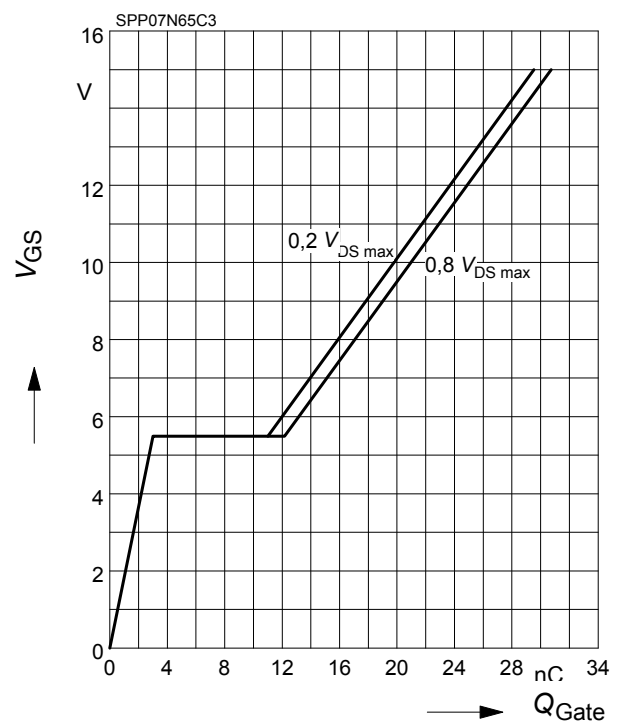
parameter:  $t_p = 10\text{ }\mu\text{s}$



### 12 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

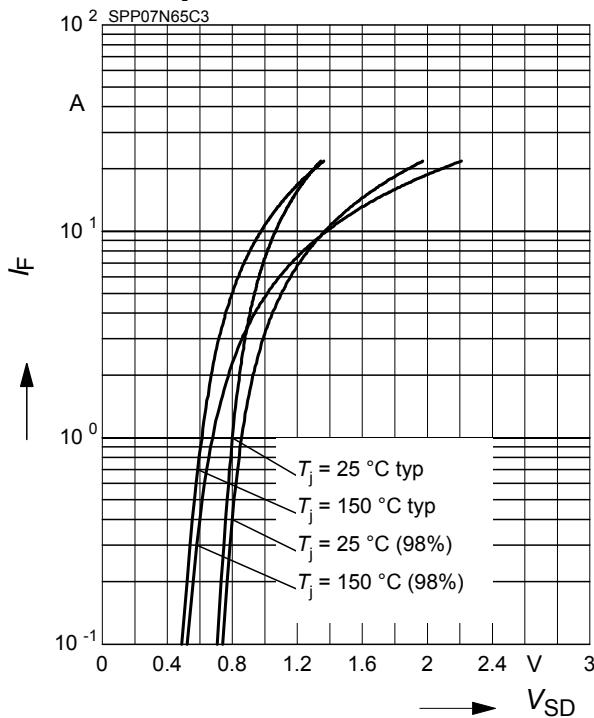
parameter:  $I_D = 7.3\text{ A}$  pulsed



### 13 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

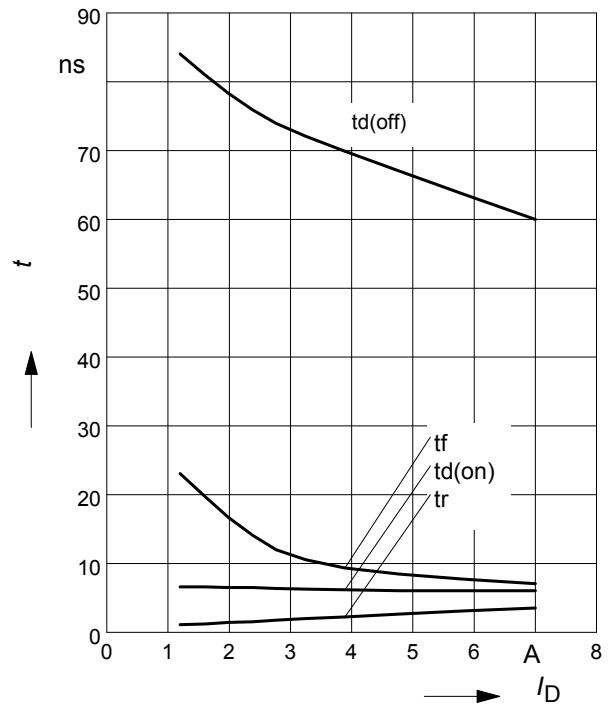
parameter:  $T_j$ ,  $t_p = 10 \mu s$



### 14 Typ. switching time

$$t = f(I_D), \text{ inductive load, } T_j = 125^\circ C$$

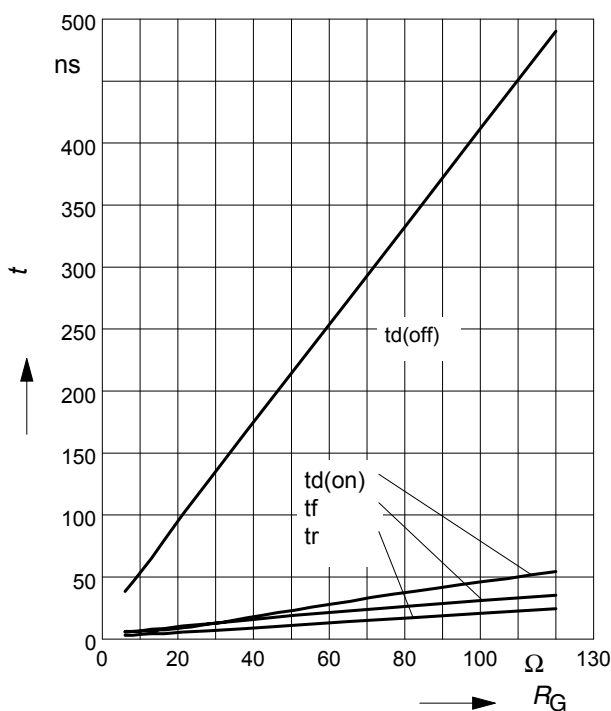
par.:  $V_{DS} = 380V$ ,  $V_{GS} = 0/+13V$ ,  $R_G = 12\Omega$



### 15 Typ. switching time

$$t = f(R_G), \text{ inductive load, } T_j = 125^\circ C$$

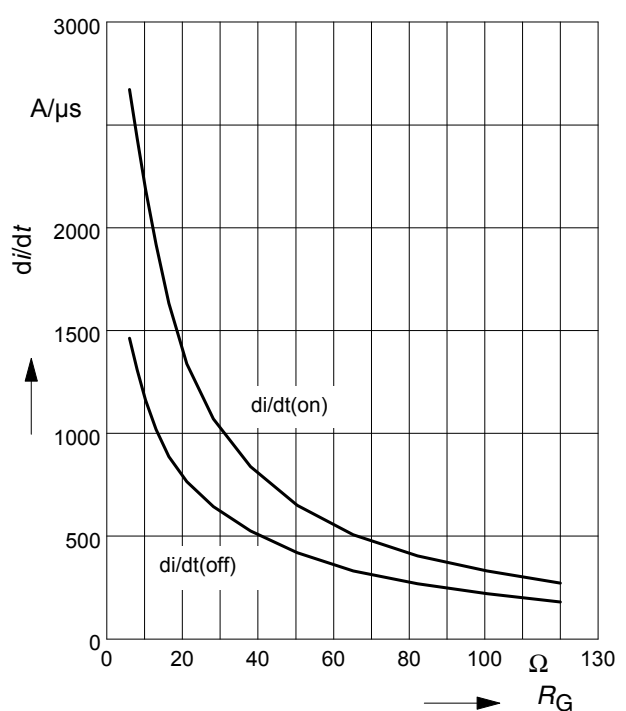
par.:  $V_{DS} = 380V$ ,  $V_{GS} = 0/+13V$ ,  $I_D = 7.3 A$



### 16 Typ. drain current slope

$$di/dt = f(R_G), \text{ inductive load, } T_j = 125^\circ C$$

par.:  $V_{DS} = 380V$ ,  $V_{GS} = 0/+13V$ ,  $I_D = 7.3A$

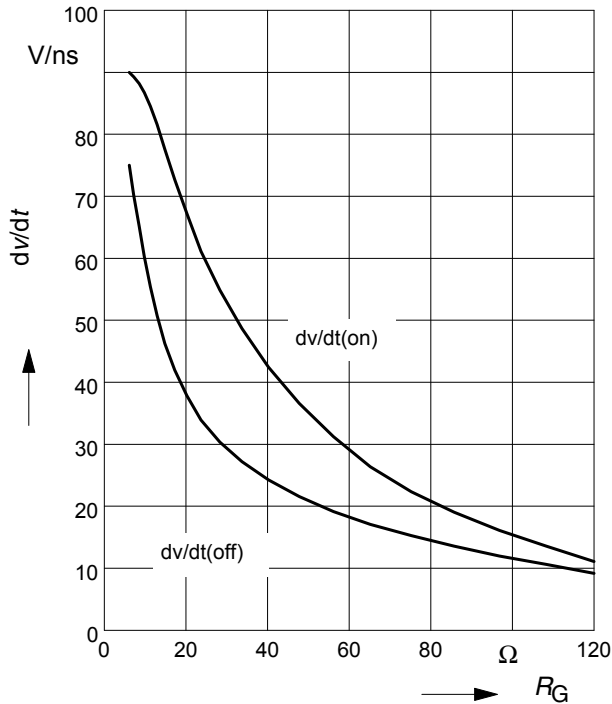




### 17 Typ. drain source voltage slope

$dv/dt = f(R_G)$ , inductive load,  $T_j = 125^\circ\text{C}$

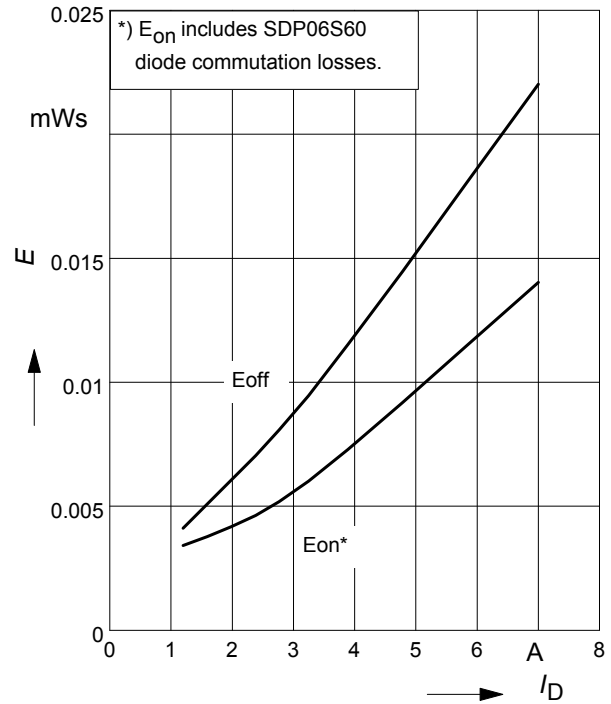
par.:  $V_{DS}=380\text{V}$ ,  $V_{GS}=0/+13\text{V}$ ,  $I_D=7.3\text{A}$



### 18 Typ. switching losses

$E = f(I_D)$ , inductive load,  $T_j=125^\circ\text{C}$

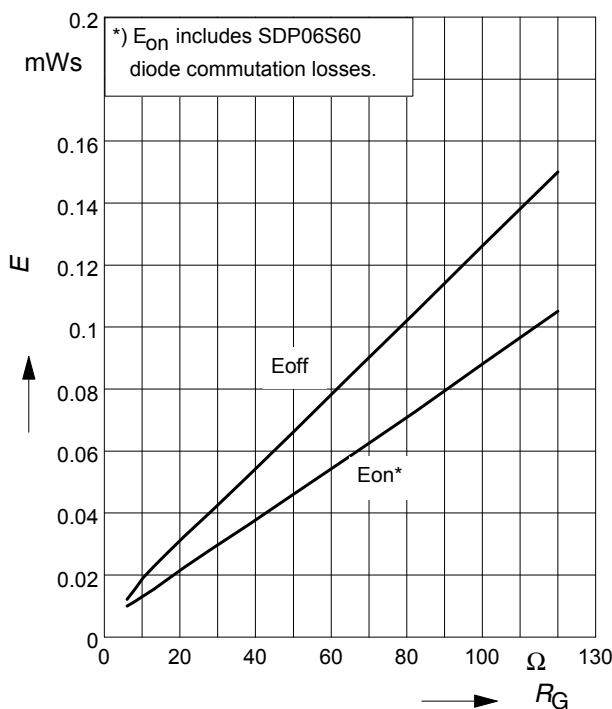
par.:  $V_{DS}=380\text{V}$ ,  $V_{GS}=0/+13\text{V}$ ,  $R_G=12\Omega$



### 19 Typ. switching losses

$E = f(R_G)$ , inductive load,  $T_j=125^\circ\text{C}$

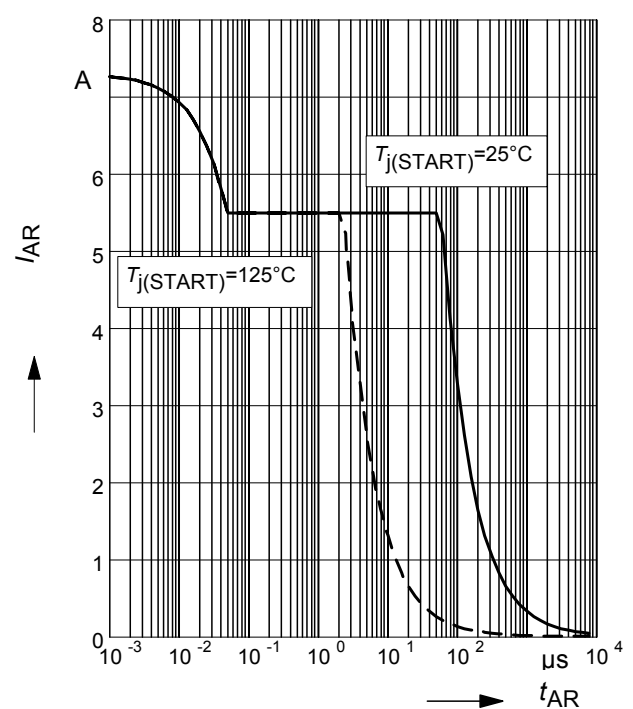
par.:  $V_{DS}=380\text{V}$ ,  $V_{GS}=0/+13\text{V}$ ,  $I_D=11\text{A}$



### 20 Avalanche SOA

$I_{AR} = f(t_{AR})$

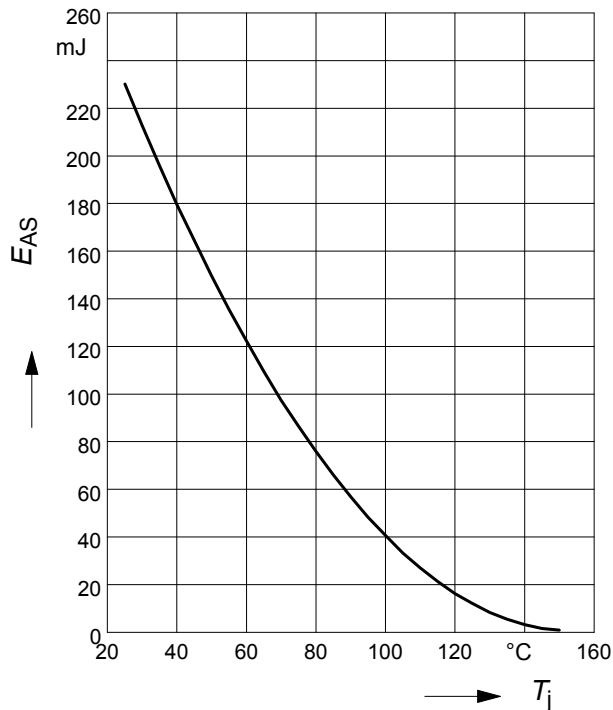
par.:  $T_j \leq 150^\circ\text{C}$



## 21 Avalanche energy

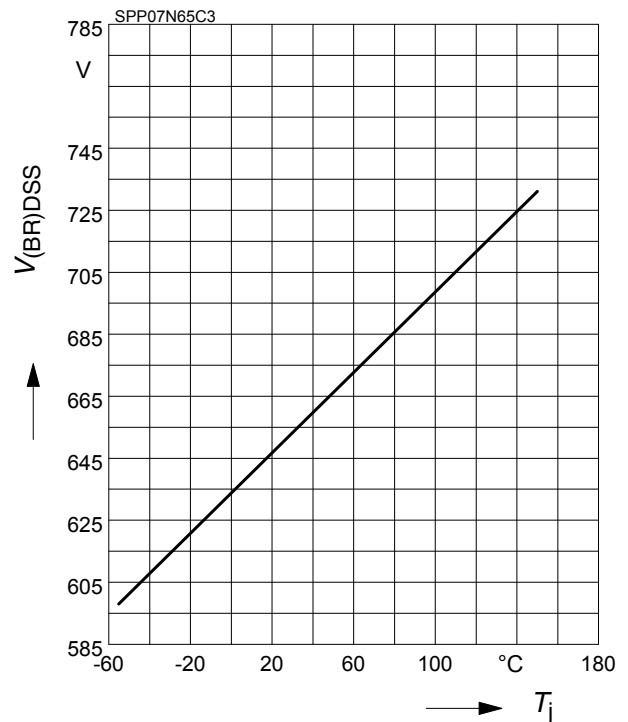
$$E_{AS} = f(T_j)$$

par.:  $I_D = 1.5 \text{ A}$ ,  $V_{DD} = 50 \text{ V}$



## 22 Drain-source breakdown voltage

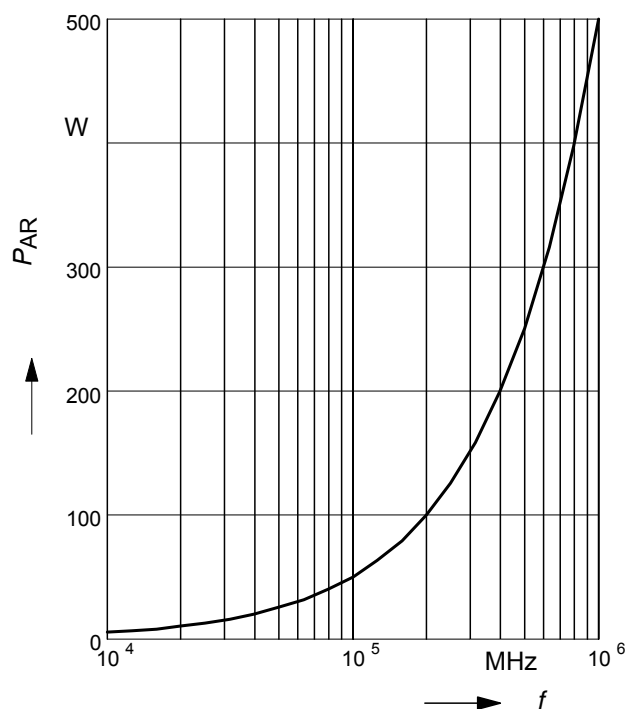
$$V_{(BR)DSS} = f(T_j)$$



## 23 Avalanche power losses

$$P_{AR} = f(f)$$

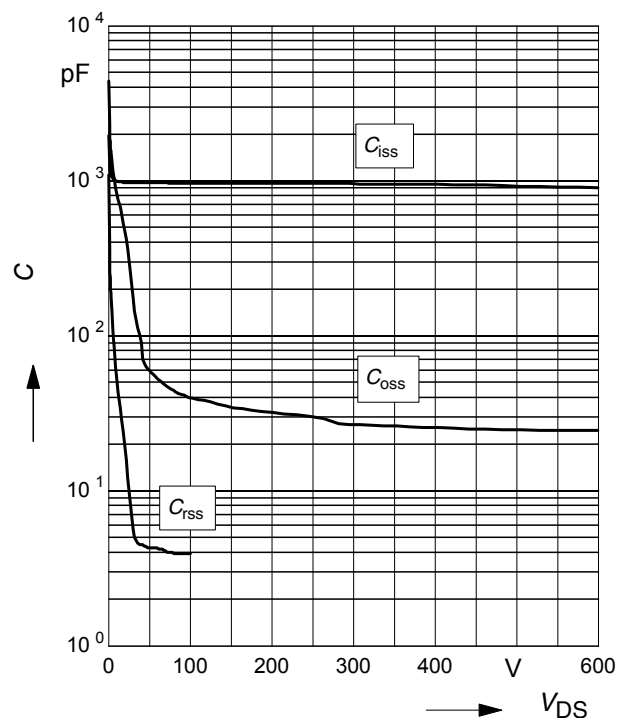
parameter:  $E_{AR} = 0.5 \text{ mJ}$



## 24 Typ. capacitances

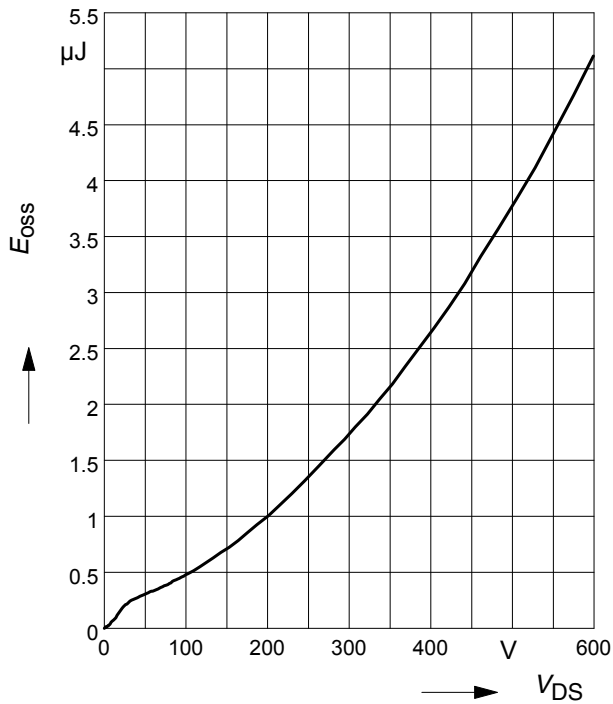
$$C = f(V_{DS})$$

parameter:  $V_{GS} = 0 \text{ V}$ ,  $f = 1 \text{ MHz}$

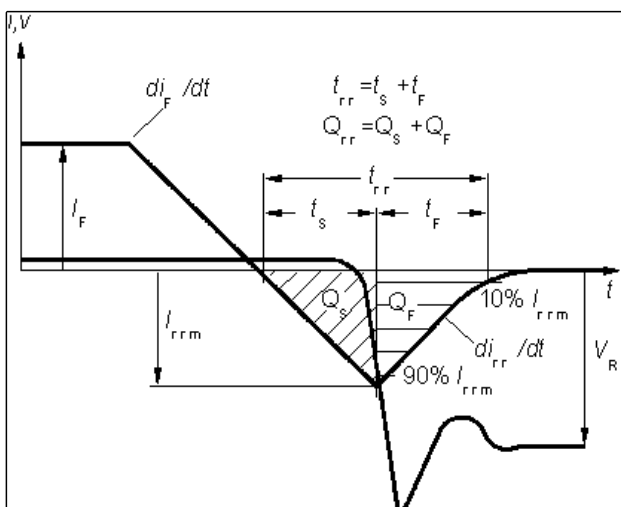


## 25 Typ. $C_{oss}$ stored energy

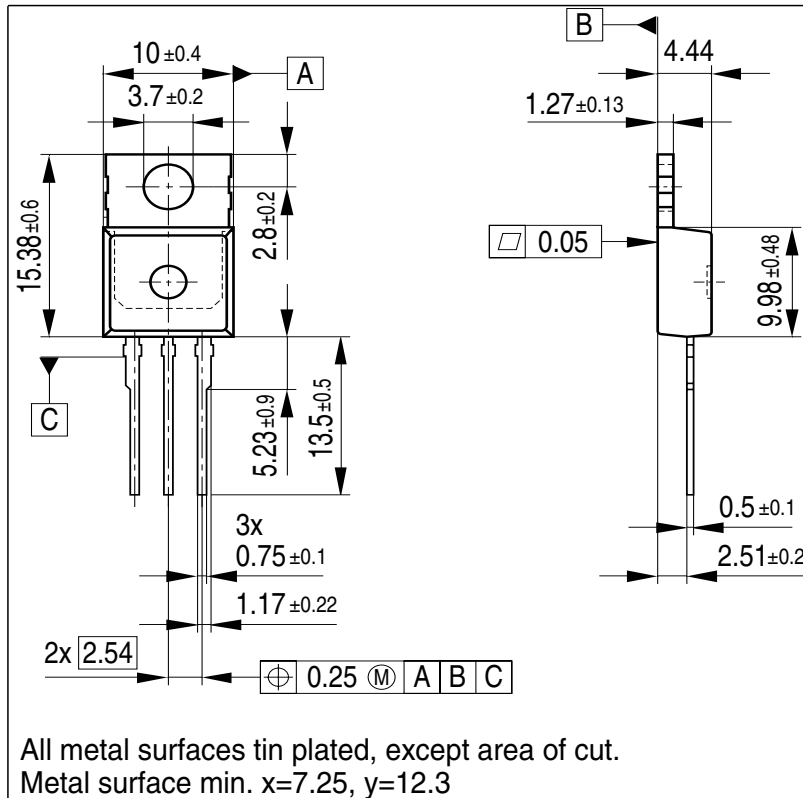
$$E_{oss} = f(V_{DS})$$



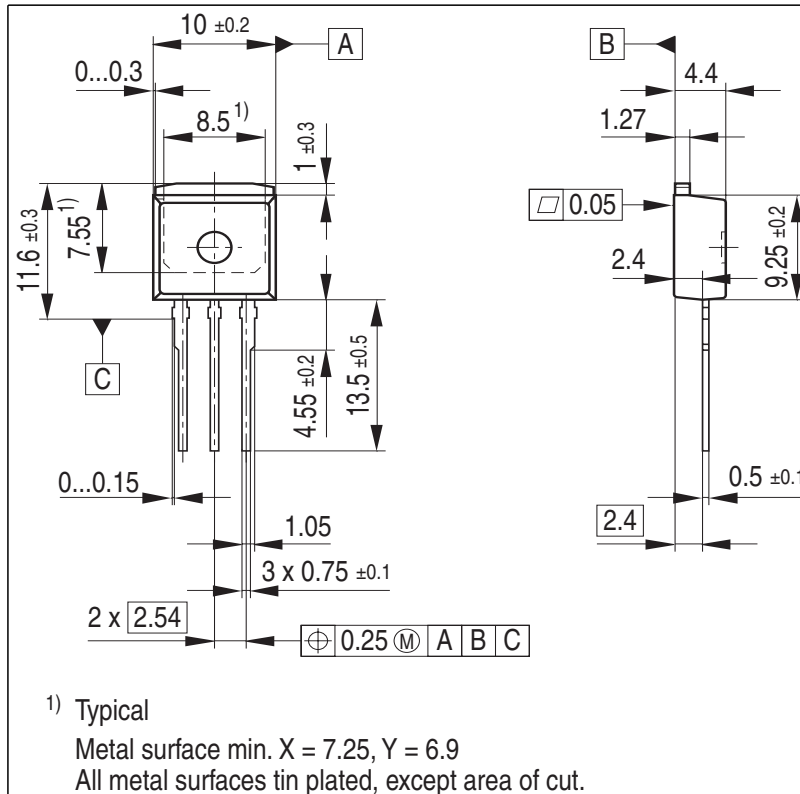
## Definition of diodes switching characteristics



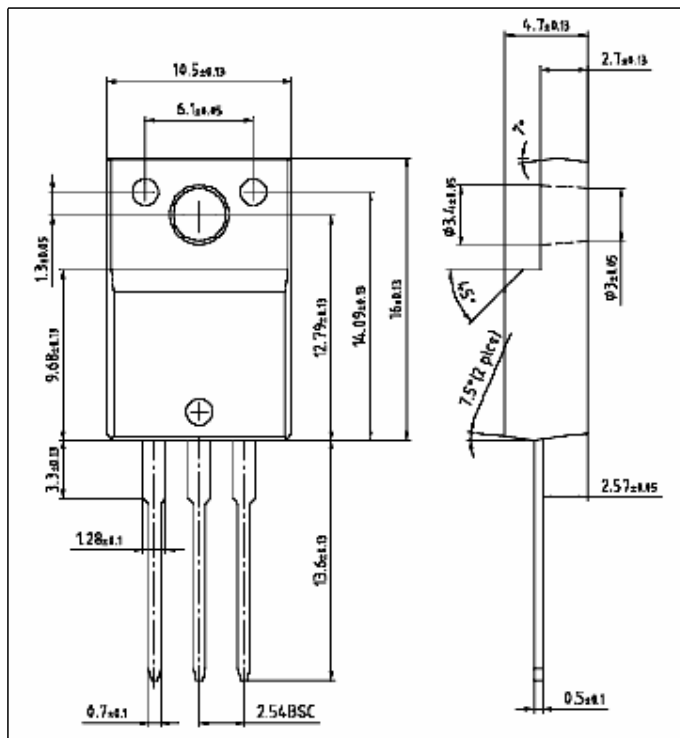
P-TO-220-3-1



**P-TO-262-3-1 (I<sup>2</sup>-PAK)**



**P-TO-220-3-31 (FullPAK)**



Please refer to mounting instructions (application note AN-TO220-3-31-01)

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